

Transistors with Built-in Resistor **DRC5143E0L**

DRC5143E0L Silicon NPN epitaxial planar type

For digital circuits Complementary to DRA5143E DRC2143E in SMini3 type package

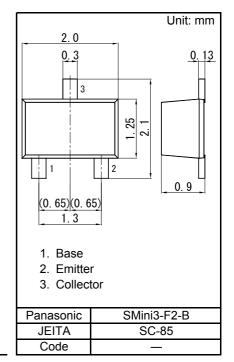
Features

- Low collector-emitter saturation voltage Vce(sat) ٠
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)
- Marking Symbol: N5

Packaging

Collector current Total power dissipation Junction temperature

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)



	_	Unit	Rating	Symbol
		V	50	VCBO
Connection	Internal	V	50	VCEO
		mA	100	IC
C C	R ₁	mW	150	PT
ι τη	B ↔ — —	°C	150	Tj
	R ₂	°C	-40 to +85	Topr
- OE		°C	-55 to +150	Tstg
R1 4.7	Resistance			

value

R2

4.7

Operating ambient temperature Storage temperature

Absolute Maximum Ratings Ta = 25 °C

Parameter

Collector-base voltage (Emitter open)

Collector-emitter voltage (Base open)

Electrical Characteristics	$T_2 = 25 \circ C + 3 \circ C$

Electrical characteristics $Ta = 25 \circ C \pm 3 \circ C$									
Symbol	Conditions	Min	Тур	Max	Unit				
VCBO	IC = 10 μA, IE = 0	50			V				
VCEO	IC = 2 mA, IB = 0	50			V				
ICBO	VCB = 50 V, IE = 0			0.1	μA				
ICEO	VCE = 50 V, IB = 0			0.5	μA				
IEBO	VEB = 6 V, IC = 0			2.0	mA				
hFE	VCE = 10 V, IC = 5 mA	20			-				
VCE(sat)	IC = 10 mA, IB = 0.5 mA			0.25	V				
Vi(on)	VCE = 0.2 V, IC = 5 mA	1.9			V				
Vi(off)	VCE = 5 V, IC = 100 µA			0.8	V				
R1		-30%	4.7	+30%	kΩ				
R1/R2		0.8	1.0	1.2	-				
	Symbol VCBO ICBO ICEO IEBO hFE VCE(sat) Vi(on) Vi(off) R1	Symbol Conditions VCBO IC = 10 μ A, IE = 0 VCEO IC = 2 mA, IB = 0 ICBO VCB = 50 V, IE = 0 ICEO VCE = 50 V, IB = 0 IEBO VEB = 6 V, IC = 0 hFE VCE = 10 V, IC = 5 mA VCE(sat) IC = 10 mA, IB = 0.5 mA Vi(on) VCE = 5 V, IC = 100 μ A R1 R1	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

kΩ

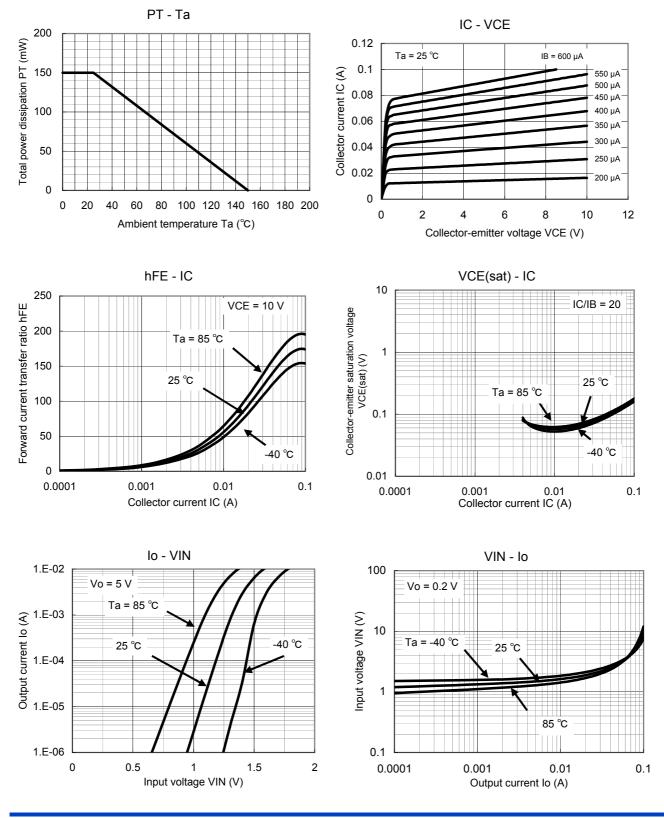
kΩ



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Technical Data (reference)



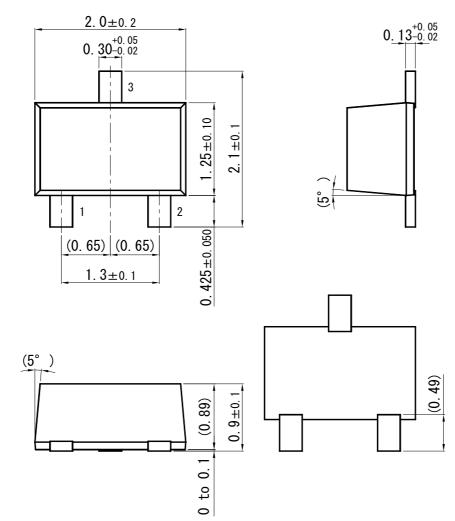
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Established : 2009-10-15 Revised : 2014-03-14

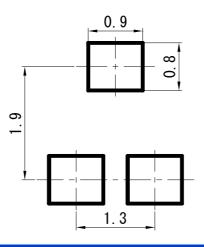


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Unit: mm



Land Pattern (Reference) (Unit: mm)



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SMini3-F2-B

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